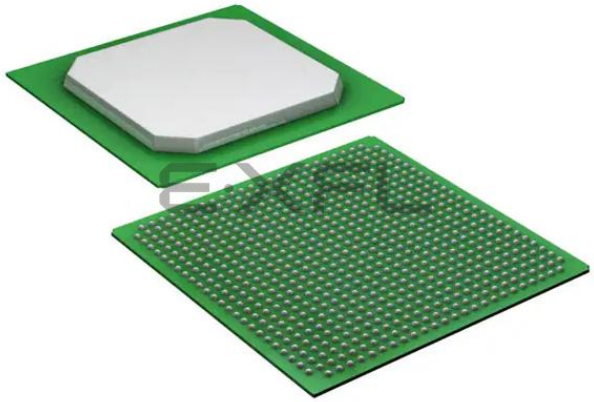

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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	1057
Number of Logic Elements/Cells	10570
Total RAM Bits	920448
Number of I/O	345
Number of Gates	-
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-BGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep1s10b672c7

Chapter 3. Configuration & Testing

Chapter 4. DC & Switching Characteristics

Table 2–9. M-RAM Block Configurations (True Dual-Port)				
Port A	Port B			
	64K × 9	32K × 18	16K × 36	8K × 72
64K × 9	✓	✓	✓	✓
32K × 18	✓	✓	✓	✓
16K × 36	✓	✓	✓	✓
8K × 72	✓	✓	✓	✓

The read and write operation of the memory is controlled by the WREN signal, which sets the ports into either read or write modes. There is no separate read enable (RE) signal.

Writing into RAM is controlled by both the WREN and byte enable (byteena) signals for each port. The default value for the byteena signal is high, in which case writing is controlled only by the WREN signal. The byte enables are available for the ×18, ×36, and ×72 modes. In the ×144 simple dual-port mode, the two sets of byteena signals (byteena_a and byteena_b) are combined to form the necessary 16 byte enables. Tables 2–10 and 2–11 summarize the byte selection.

Table 2–10. Byte Enable for M-RAM Blocks *Notes (1), (2)*			
byteena[3..0]	datain ×18	datain ×36	datain ×72
[0] = 1	[8..0]	[8..0]	[8..0]
[1] = 1	[17..9]	[17..9]	[17..9]
[2] = 1	–	[26..18]	[26..18]
[3] = 1	–	[35..27]	[35..27]
[4] = 1	–	–	[44..36]
[5] = 1	–	–	[53..45]
[6] = 1	–	–	[62..54]
[7] = 1	–	–	[71..63]

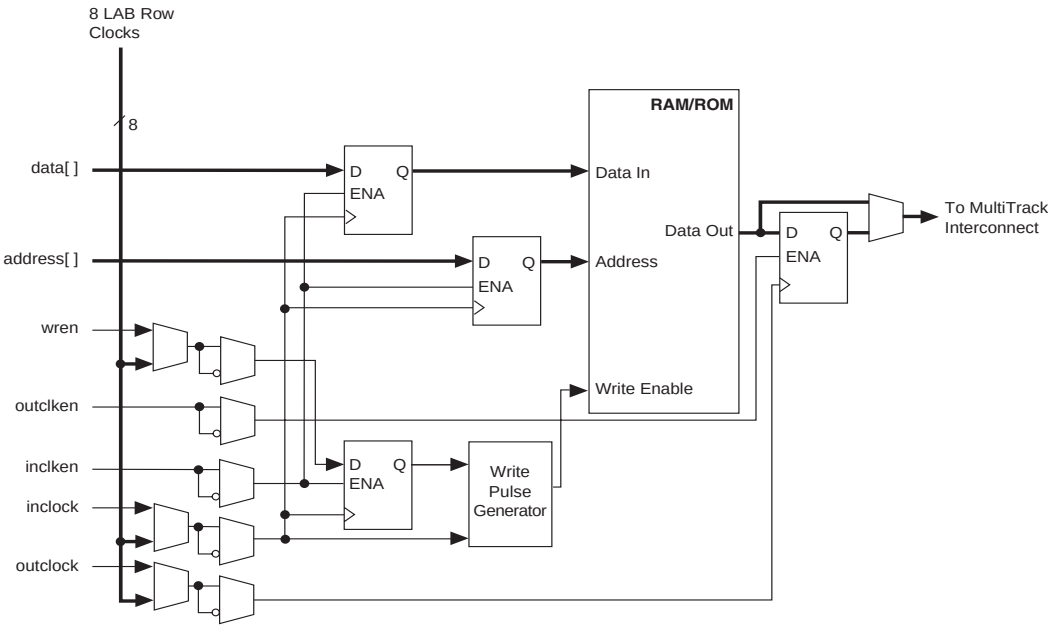
Read/Write Clock Mode

The memory blocks implement read/write clock mode for simple dual-port memory. You can use up to two clocks in this mode. The write clock controls the block's data inputs, `wraddress`, and `wren`. The read clock controls the data output, `rdaddress`, and `rden`. The memory blocks support independent clock enables for each clock and asynchronous clear signals for the read- and write-side registers. Figure 2–27 shows a memory block in read/write clock mode.

Single-Port Mode

The memory blocks also support single-port mode, used when simultaneous reads and writes are not required. See Figure 2–28. A single block in a memory block can support up to two single-port mode RAM blocks in the M4K RAM blocks if each RAM block is less than or equal to 2K bits in size.

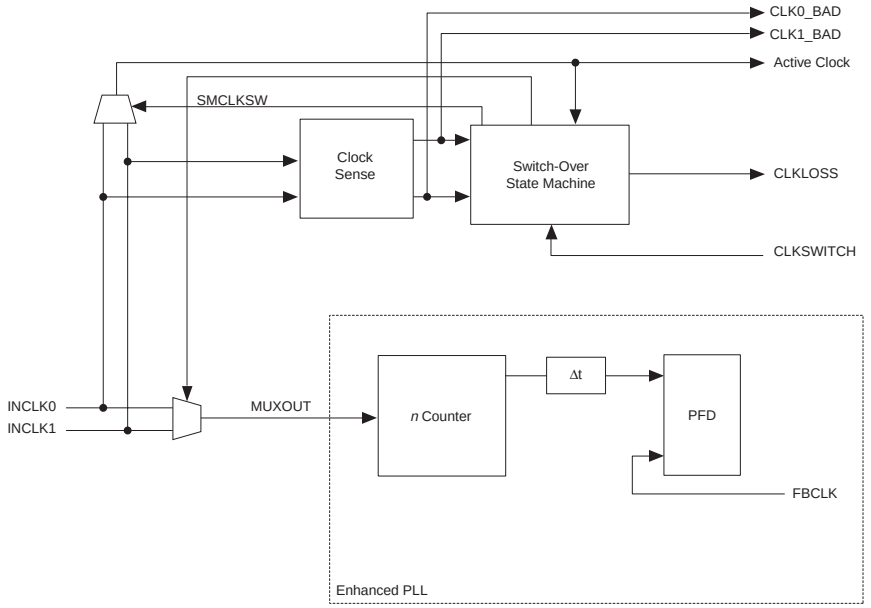
Figure 2–28. Single-Port Mode Note (1)



Note to Figure 2–28:

(1) Violating the setup or hold time on the address registers could corrupt the memory contents. This applies to both read and write operations.

Figure 2–53. Clock Switchover Circuitry



There are two possible ways to use the clock switchover feature.

- Use automatic switchover circuitry for switching between inputs of the same frequency. For example, in applications that require a redundant clock with the same frequency as the primary clock, the switchover state machine generates a signal that controls the multiplexer select input on the bottom of Figure 2–53. In this case, the secondary clock becomes the reference clock for the PLL.
- Use the `clkswitch` input for user- or system-controlled switch conditions. This is possible for same-frequency switchover or to switch between inputs of different frequencies. For example, if `inclk0` is 66 MHz and `inclk1` is 100 MHz, you must control the switchover because the automatic clock-sense circuitry cannot monitor primary and secondary clock frequencies with a frequency difference of more than ±20%. This feature is useful when clock sources can originate from multiple cards on the backplane, requiring a system-controlled switchover between frequencies of operation. You can use `clkswitch` together with the lock signal to trigger the switch from a clock that is running but becomes unstable and cannot be locked onto.

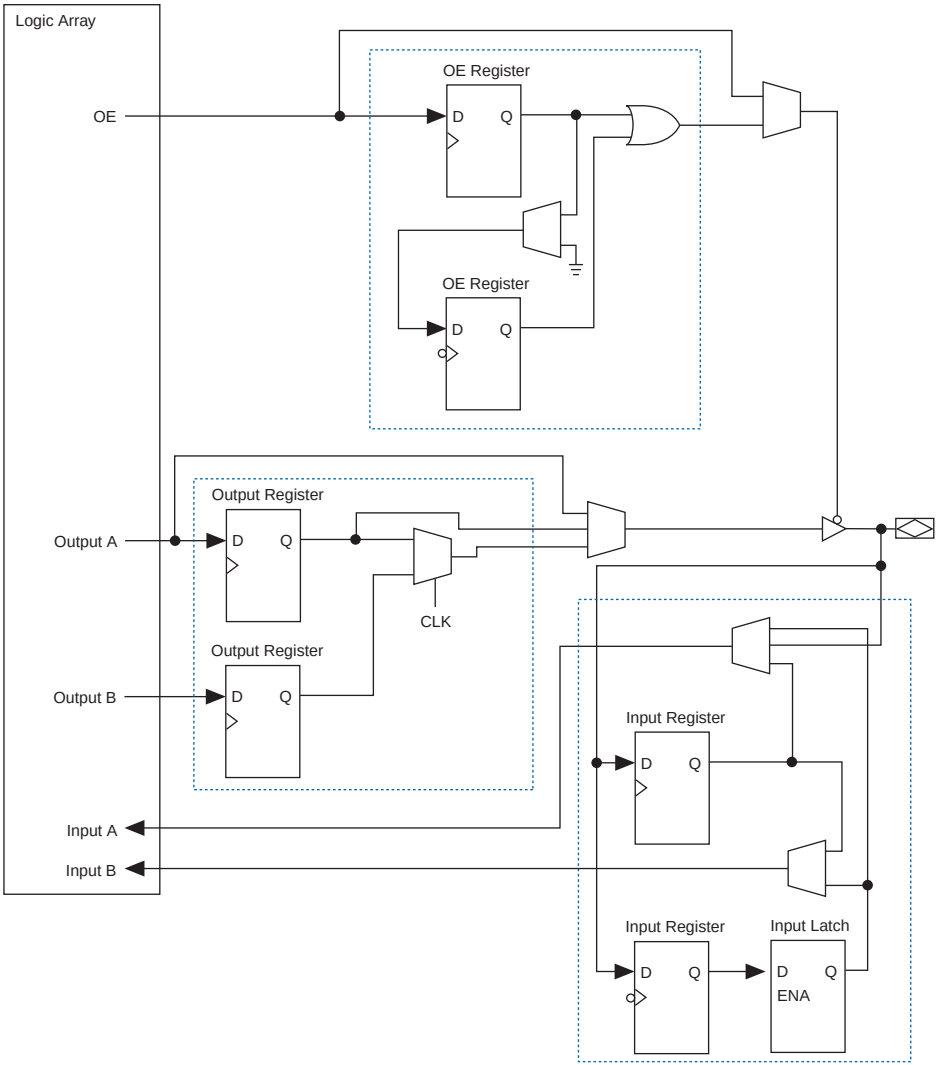
Any of the four external output counters can drive the single-ended or differential clock outputs for PLLs 5 and 6. This means one counter or frequency can drive all output pins available from PLL 5 or PLL 6. Each pair of output pins (four pins total) has dedicated VCC and GND pins to reduce the output clock's overall jitter by providing improved isolation from switching I/O pins.

For PLLs 5 and 6, each pin of a single-ended output pair can either be in phase or 180° out of phase. The clock output pin pairs support the same I/O standards as standard output pins (in the top and bottom banks) as well as LVDS, LVPECL, 3.3-V PCML, HyperTransport technology, differential HSTL, and differential SSTL. Table 2–20 shows which I/O standards the enhanced PLL clock pins support. When in single-ended or differential mode, the two outputs operate off the same power supply. Both outputs use the same standards in single-ended mode to maintain performance. You can also use the external clock output pins as user output pins if external enhanced PLL clocking is not needed.

Table 2–20. I/O Standards Supported for Enhanced PLL Pins (Part 1 of 2)

I/O Standard	Input			Output
	INCLK	FBIN	PLLENABLE	EXTCLK
LVTTL	✓	✓	✓	✓
LVCMOS	✓	✓	✓	✓
2.5 V	✓	✓		✓
1.8 V	✓	✓		✓
1.5 V	✓	✓		✓
3.3-V PCI	✓	✓		✓
3.3-V PCI-X 1.0	✓	✓		✓
LVPECL	✓	✓		✓
3.3-V PCML	✓	✓		✓
LVDS	✓	✓		✓
HyperTransport technology	✓	✓		✓
Differential HSTL	✓			✓
Differential SSTL				✓
3.3-V GTL	✓	✓		✓
3.3-V GTL+	✓	✓		✓
1.5-V HSTL Class I	✓	✓		✓

Figure 2–59. Stratix IOE Structure



The IOEs are located in I/O blocks around the periphery of the Stratix device. There are up to four IOEs per row I/O block and six IOEs per column I/O block. The row I/O blocks drive row, column, or direct link interconnects. The column I/O blocks drive column interconnects. Figure 2–60 shows how a row I/O block connects to the logic array. Figure 2–61 shows how a column I/O block connects to the logic array.

Tables 2–25 and 2–26 show the performance specification for DDR SDRAM, RLDRAM II, QDR SRAM, QDRII SRAM, and ZBT SRAM interfaces in EP1S10 through EP1S40 devices and in EP1S60 and EP1S80 devices. The DDR SDRAM and QDR SRAM numbers in Table 2–25 have been verified with hardware characterization with third-party DDR SDRAM and QDR SRAM devices over temperature and voltage extremes.

Table 2–25. External RAM Support in EP1S10 through EP1S40 Devices

DDR Memory Type	I/O Standard	Maximum Clock Rate (MHz)						
		-5 Speed Grade	-6 Speed Grade		-7 Speed Grade		-8 Speed Grade	
		Flip-Chip	Flip-Chip	Wire-Bond	Flip-Chip	Wire-Bond	Flip-Chip	Wire-Bond
DDR SDRAM *(1)*, *(2)*	SSTL-2	200	167	133	133	100	100	100
DDR SDRAM - side banks *(2)*, *(3)*, *(4)*	SSTL-2	150	133	110	133	100	100	100
RLDRAM II *(4)*	1.8-V HSTL	200	*(5)*	*(5)*	*(5)*	*(5)*	*(5)*	*(5)*
QDR SRAM *(6)*	1.5-V HSTL	167	167	133	133	100	100	100
QDRII SRAM *(6)*	1.5-V HSTL	200	167	133	133	100	100	100
ZBT SRAM *(7)*	LVTTL	200	200	200	167	167	133	133

Notes to Table 2–25:

(1) These maximum clock rates apply if the Stratix device uses DQS phase-shift circuitry to interface with DDR SDRAM. DQS phase-shift circuitry is only available in the top and bottom I/O banks (I/O banks 3, 4, 7, and 8).

(2) For more information on DDR SDRAM, see *AN 342: Interfacing DDR SDRAM with Stratix & Stratix GX Devices.*

(3) DDR SDRAM is supported on the Stratix device side I/O banks (I/O banks 1, 2, 5, and 6) without dedicated DQS phase-shift circuitry. The read DQS signal is ignored in this mode.

(4) These performance specifications are preliminary.

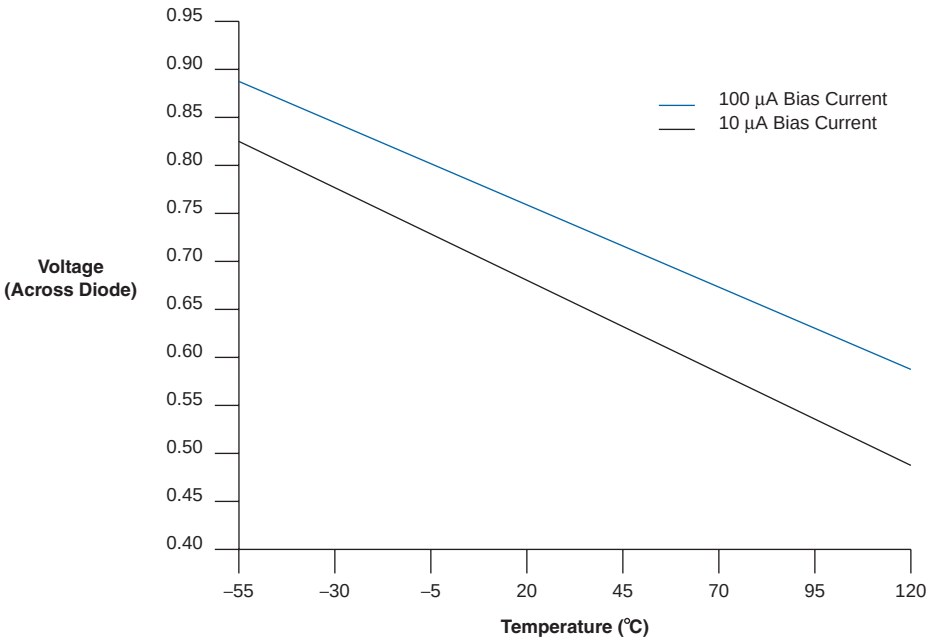
(5) This device does not support RLDRAM II.

(6) For more information on QDR or QDRII SRAM, see *AN 349: QDR SRAM Controller Reference Design for Stratix & Stratix GX Devices*.

(7) For more information on ZBT SRAM, see *AN 329: ZBT SRAM Controller Reference Design for Stratix & Stratix GX Devices*.

The temperature-sensing diode works for the entire operating range shown in Figure 3–6.

Figure 3–6. Temperature vs. Temperature-Sensing Diode Voltage



Performance

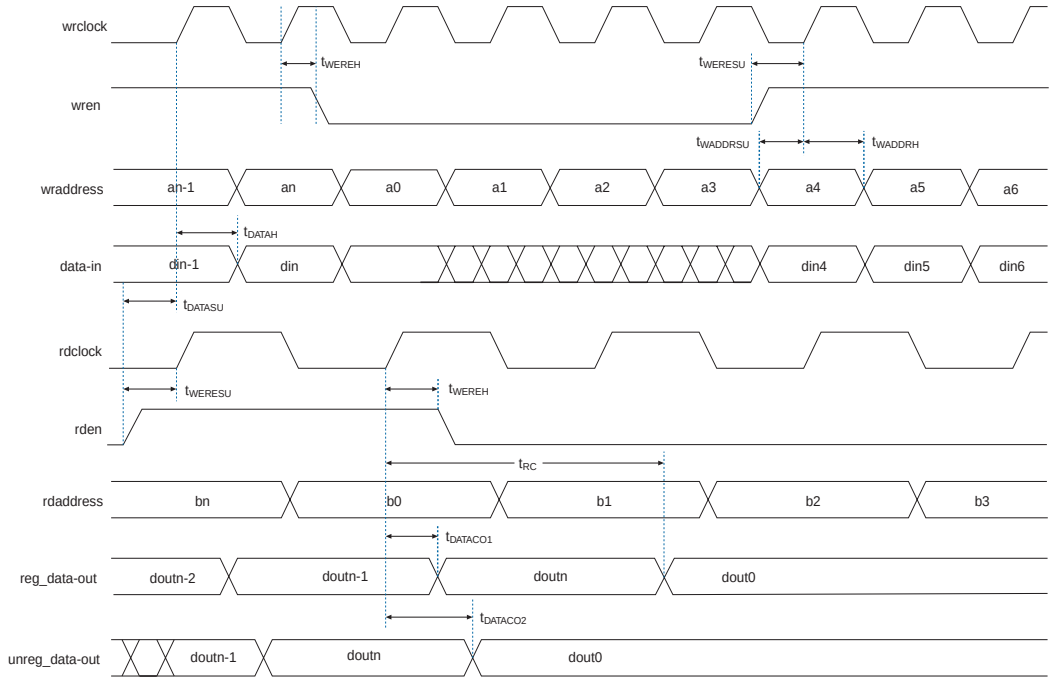
Table 4–36 shows Stratix performance for some common designs. All performance values were obtained with Quartus II software compilation of LPM, or MegaCore® functions for the FIR and FFT designs.

Table 4–36. Stratix Performance (Part 1 of 2) Notes (1), (2)

Applications		Resources Used			Performance				
		LEs	TriMatrix Memory Blocks	DSP Blocks	-5 Speed Grade	-6 Speed Grade	-7 Speed Grade	-8 Speed Grade	Units
LE	16-to-1 multiplexer *(1)*	22	0	0	407.83	324.56	288.68	228.67	MHz
	32-to-1 multiplexer *(3)*	46	0	0	318.26	255.29	242.89	185.18	MHz
	16-bit counter	16	0	0	422.11	422.11	390.01	348.67	MHz
	64-bit counter	64	0	0	321.85	290.52	261.23	220.5	MHz
TriMatrix memory M512 block	Simple dual-port RAM 32 × 18 bit	0	1	0	317.76	277.62	241.48	205.21	MHz
	FIFO 32 × 18 bit	30	1	0	319.18	278.86	242.54	206.14	MHz
TriMatrix memory M4K block	Simple dual-port RAM 128 × 36 bit	0	1	0	290.86	255.55	222.27	188.89	MHz
	True dual-port RAM 128 × 18 bit	0	1	0	290.86	255.55	222.27	188.89	MHz
	FIFO 128 × 36 bit	34	1	0	290.86	255.55	222.27	188.89	MHz
TriMatrix memory M-RAM block	Single port RAM 4K × 144 bit	1	1	0	255.95	223.06	194.06	164.93	MHz
	Simple dual-port RAM 4K × 144 bit	0	1	0	255.95	233.06	194.06	164.93	MHz
	True dual-port RAM 4K × 144 bit	0	1	0	255.95	233.06	194.06	164.93	MHz
	Single port RAM 8K × 72 bit	0	1	0	278.94	243.19	211.59	179.82	MHz
	Simple dual-port RAM 8K × 72 bit	0	1	0	255.95	223.06	194.06	164.93	MHz
	True dual-port RAM 8K × 72 bit	0	1	0	255.95	223.06	194.06	164.93	MHz
	Single port RAM 16K × 36 bit	0	1	0	280.66	254.32	221.28	188.00	MHz
	Simple dual-port RAM 16K × 36 bit	0	1	0	269.83	237.69	206.82	175.74	MHz

Figure 4–3 shows the TriMatrix memory waveforms for the M512, M4K, and M-RAM timing parameters shown in Tables 4–40 through 4–42.

Figure 4–3. Dual-Port RAM Timing Microparameter Waveform



Internal timing parameters are specified on a speed grade basis independent of device density. Tables 4–44 through 4–50 show the internal timing microparameters for LEs, IOEs, TriMatrix memory structures, DSP blocks, and MultiTrack interconnects.

Table 4–43. Routing Delay Internal Timing Microparameter Descriptions (Part 1 of 2)

Symbol	Parameter
t_{R4}	Delay for an R4 line with average loading; covers a distance of four LAB columns.
t_{R8}	Delay for an R8 line with average loading; covers a distance of eight LAB columns.
t_{R24}	Delay for an R24 line with average loading; covers a distance of 24 LAB columns.

Table 4–59. EP1S10 External I/O Timing on Row Pins Using Regional Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.161		2.336		2.685		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.434	4.889	2.434	5.226	2.434	5.643	NA	NA	ns
t_{XZ}	2.461	4.493	2.461	5.282	2.461	5.711	NA	NA	ns
t_{ZX}	2.461	4.493	2.461	5.282	2.461	5.711	NA	NA	ns
$t_{INSUPLL}$	1.057		1.172		1.315		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA		ns
$t_{OUTCOPLL}$	1.327	2.773	1.327	2.848	1.327	2.940	NA	NA	ns
t_{XZPLL}	1.354	2.827	1.354	2.904	1.354	3.008	NA	NA	ns
t_{ZXPLL}	1.354	2.827	1.354	2.904	1.354	3.008	NA	NA	ns

Table 4–60. EP1S10 External I/O Timing on Row Pins Using Global Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.787		1.944		2.232		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.647	5.263	2.647	5.618	2.647	6.069	NA	NA	ns
t_{XZ}	2.674	5.317	2.674	5.674	2.674	6.164	NA	NA	ns
t_{ZX}	2.674	5.317	2.674	5.674	2.674	6.164	NA	NA	ns
$t_{INSUPLL}$	1.371		1.1472		1.654		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA		ns
$t_{OUTCOPLL}$	1.144	2.459	1.144	2.548	1.144	2.601	NA	NA	ns
t_{XZPLL}	1.171	2.513	1.171	2.604	1.171	2.669	NA	NA	ns
t^{ZXPLL}	1.171	2.513	1.171	2.604	1.171	2.669	NA	NA	ns

Note to Tables 4–55 to 4–60:

(1) Only EP1S25, EP1S30, and EP1S40 have speed grade of -8.

Tables 4–61 through 4–66 show the external timing parameters on column and row pins for EP1S20 devices.

Table 4–61. EP1S20 External I/O Timing on Column Pins Using Fast Regional Clock Networks Note (1)

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.065		2.245		2.576		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.283	4.622	2.283	4.916	2.283	5.310	NA	NA	ns
t_{XZ}	2.223	4.496	2.223	4.784	2.223	5.186	NA	NA	ns
t_{ZX}	2.223	4.496	2.223	4.784	2.223	5.186	NA	NA	ns

Table 4–62. EP1S20 External I/O Timing on Column Pins Using Regional Clock Networks Note (1)

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.541		1.680		1.931		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.597	5.146	2.597	5.481	2.597	5.955	NA	NA	ns
t_{XZ}	2.537	5.020	2.537	5.349	2.537	5.831	NA	NA	ns
t_{ZX}	2.537	5.020	2.537	5.349	2.537	5.831	NA	NA	ns
$t_{INSUPLL}$	0.777		0.818		0.937		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA		ns
$t_{OUTCOPLL}$	1.296	2.690	1.296	2.801	1.296	2.876	NA	NA	ns
t_{XZPLL}	1.236	2.564	1.236	2.669	1.236	2.752	NA	NA	ns
t_{ZXPLL}	1.236	2.564	1.236	2.669	1.236	2.752	NA	NA	ns

Table 4–65. EP1S20 External I/O Timing on Row Pins Using Regional Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.815		1.967		2.258		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.633	5.235	2.663	5.595	2.663	6.070	NA	NA	ns
t_{XZ}	2.660	5.289	2.660	5.651	2.660	6.138	NA	NA	ns
t_{ZX}	2.660	5.289	2.660	5.651	2.660	6.138	NA	NA	ns
$t_{INSUPLL}$	1.060		1.112		1.277		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA		ns
$t_{OUTCOPLL}$	1.325	2.770	1.325	2.908	1.325	2.978	NA	NA	ns
t_{XZPLL}	1.352	2.824	1.352	2.964	1.352	3.046	NA	NA	ns
t_{ZXPLL}	1.352	2.824	1.352	2.964	1.352	3.046	NA	NA	ns

Table 4–66. EP1S20 External I/O Timing on Row Pins Using Global Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.742		1.887		2.170		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.674	5.308	2.674	5.675	2.674	6.158	NA	NA	ns
t_{XZ}	2.701	5.362	2.701	5.731	2.701	6.226	NA	NA	ns
t_{ZX}	2.701	5.362	2.701	5.731	2.701	6.226	NA	NA	ns
$t_{INSUPLL}$	1.353		1.418		1.613		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA		ns
$t_{OUTCOPLL}$	1.158	2.447	1.158	2.602	1.158	2.642	NA	NA	ns
t_{XZPLL}	1.185	2.531	1.158	2.602	1.185	2.710	NA	NA	ns
t_{ZXPLL}	1.185	2.531	1.158	2.602	1.185	2.710	NA	NA	ns

Note to Tables 4–61 to 4–66:

(1) Only EP1S25, EP1S30, and EP1S40 have a speed grade of -8.

Tables 4–67 through 4–72 show the external timing parameters on column and row pins for EP1S25 devices.

Table 4–67. EP1S25 External I/O Timing on Column Pins Using Fast Regional Clock Networks

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.412		2.613		2.968		3.468		ns
t_{INH}	0.000		0.000		0.000		0.000		ns
t_{OUTCO}	2.196	4.475	2.196	4.748	2.196	5.118	2.196	5.603	ns
t_{XZ}	2.136	4.349	2.136	4.616	2.136	4.994	2.136	5.488	ns
t_{ZX}	2.136	4.349	2.136	4.616	2.136	4.994	2.136	5.488	ns

Table 4–68. EP1S25 External I/O Timing on Column Pins Using Regional Clock Networks

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.535		1.661		1.877		2.125		ns
t_{INH}	0.000		0.000		0.000		0.000		ns
t_{OUTCO}	2.739	5.396	2.739	5.746	2.739	6.262	2.739	6.946	ns
t_{XZ}	2.679	5.270	2.679	5.614	2.679	6.138	2.679	6.831	ns
t_{ZX}	2.679	5.270	2.679	5.614	2.679	6.138	2.679	6.831	ns
$t_{INSUPLL}$	0.934		0.980		1.092		1.231		ns
t_{INHPLL}	0.000		0.000		0.000		0.000		ns
$t_{OUTCOPLL}$	1.316	2.733	1.316	2.839	1.316	2.921	1.316	3.110	ns
t^{XZPLL}	1.256	2.607	1.256	2.707	1.256	2.797	1.256	2.995	ns
t_{ZXPLL}	1.256	2.607	1.256	2.707	1.256	2.797	1.256	2.995	ns

Tables 4–85 through 4–90 show the external timing parameters on column and row pins for EP1S60 devices.

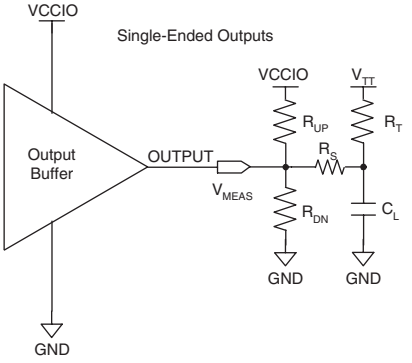
Table 4–85. EP1S60 External I/O Timing on Column Pins Using Fast Regional Clock Networks Note (1)

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	3.029		3.277		3.733		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.446	4.871	2.446	5.215	2.446	5.685	NA	NA	ns
t_{XZ}	2.386	4.745	2.386	5.083	2.386	5.561	NA	NA	ns
t_{ZX}	2.386	4.745	2.386	5.083	2.386	5.561	NA	NA	ns

Table 4–86. EP1S60 External I/O Timing on Column Pins Using Regional Clock Networks Note (1)

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.491		2.691		3.060		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.767	5.409	2.767	5.801	2.767	6.358	NA	NA	ns
t_{XZ}	2.707	5.283	2.707	5.669	2.707	6.234	NA	NA	ns
t_{ZX}	2.707	5.283	2.707	5.669	2.707	6.234	NA	NA	ns
$t_{INSUPLL}$	1.233		1.270		1.438		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA		ns
$t_{OUTCOPLL}$	1.078	2.278	1.078	2.395	1.078	2.428	NA	NA	ns
t_{XZPLL}	1.018	2.152	1.018	2.263	1.018	2.304	NA	NA	ns
t_{ZXPLL}	1.018	2.152	1.018	2.263	1.018	2.304	NA	NA	ns

Figure 4–7. Output Delay Timing Reporting Setup Modeled by Quartus II



Notes to Figure 4–7:

(1) Output pin timing is reported at the output pin of the FPGA device. Additional delays for loading and board trace delay need to be accounted for with IBIS model simulations.

(2) V_{CCINT} is 1.42-V unless otherwise specified.

Table 4–101. Reporting Methodology For Maximum Timing For Single-Ended Output Pins (Part 1 of 2)
Notes (1), (2), (3)

I/O Standard	Loading and Termination							Measurement Point
	R_{UP} Ω	R_{DN} Ω	R_S Ω	R_T Ω	V_{CCIO} (V)	VTT (V)	C_L (pF)	V_{MEAS}
3.3-V LVTTL	–	–	0	–	2.950	2.95	10	1.500
2.5-V LVTTL	–	–	0	–	2.370	2.37	10	1.200
1.8-V LVTTL	–	–	0	–	1.650	1.65	10	0.880
1.5-V LVTTL	–	–	0	–	1.400	1.40	10	0.750
3.3-V LVCMOS	–	–	0	–	2.950	2.95	10	1.500
2.5-V LVCMOS	–	–	0	–	2.370	2.37	10	1.200
1.8-V LVCMOS	–	–	0	–	1.650	1.65	10	0.880
1.5-V LVCMOS	–	–	0	–	1.400	1.40	10	0.750
3.3-V GTL	–	–	0	25	2.950	1.14	30	0.740
2.5-V GTL	–	–	0	25	2.370	1.14	30	0.740
3.3-V GTL+	–	–	0	25	2.950	1.35	30	0.880
2.5-V GTL+	–	–	0	25	2.370	1.35	30	0.880
3.3-V SSTL-3 Class II	–	–	25	25	2.950	1.25	30	1.250

Table 4–106. Stratix I/O Standard Output Delay Adders for Fast Slew Rate on Row Pins (Part 2 of 2)

Parameter		-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
1.5-V LVTTL	2 mA		5,460		5,733		5,733		5,733	ps
	4 mA		2,690		2,824		2,824		2,824	ps
	8 mA		1,398		1,468		1,468		1,468	ps
GTL+			6		6		6		6	ps
CTT			845		887		887		887	ps
SSTL-3 Class I			638		670		670		670	ps
SSTL-3 Class II			144		151		151		151	ps
SSTL-2 Class I			604		634		634		634	ps
SSTL-2 Class II			211		221		221		221	ps
SSTL-18 Class I			955		1,002		1,002		1,002	ps
1.5-V HSTL Class I			733		769		769		769	ps
1.8-V HSTL Class I			372		390		390		390	ps
LVDS			–196		–206		–206		–206	ps
LVPECL			–148		–156		–156		–156	ps
PCML			–147		–155		–155		–155	ps
HyperTransport technology			–93		–98		–98		–98	ps

Note to Table 4–103 through 4–106:
(1) These parameters are only available on row I/O pins.

Table 4–107. Stratix I/O Standard Output Delay Adders for Slow Slew Rate on Column Pins (Part 1 of 2)

Parameter		-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
LVCMOS	2 mA		1,822		1,913		1,913		1,913	ps
	4 mA		684		718		718		718	ps
	8 mA		233		245		245		245	ps
	12 mA		1		1		1		1	ps
	24 mA		–608		–638		–638		–638	ps

Table 4–122. Stratix Maximum Output Clock Rate for PLL[5, 6, 11, 12] Pins in Wire-Bond Packages (Part 1 of 2)

I/O Standard	-6 Speed Grade	-7 Speed Grade	-8 Speed Grade	Unit
LVTTL	175	150	150	MHz
2.5 V	175	150	150	MHz
1.8 V	175	150	150	MHz
1.5 V	175	150	150	MHz
LVCMOS	175	150	150	MHz
GTL	125	100	100	MHz
GTL+	125	100	100	MHz
SSTL-3 Class I	110	90	90	MHz
SSTL-3 Class II	133	125	125	MHz
SSTL-2 Class I	166	133	133	MHz
SSTL-2 Class II	133	100	100	MHz
SSTL-18 Class I	110	100	100	MHz
SSTL-18 Class II	110	100	100	MHz
1.5-V HSTL Class I	167	167	167	MHz
1.5-V HSTL Class II	167	133	133	MHz
1.8-V HSTL Class I	167	167	167	MHz
1.8-V HSTL Class II	167	133	133	MHz
3.3-V PCI	167	167	167	MHz
3.3-V PCI-X 1.0	167	133	133	MHz
Compact PCI	175	150	150	MHz
AGP 1×	175	150	150	MHz
AGP 2×	175	150	150	MHz
CTT	125	100	100	MHz
Differential 1.5-V HSTL C1	167	133	133	MHz
Differential 1.8-V HSTL Class I	167	167	167	MHz
Differential 1.8-V HSTL Class II	167	133	133	MHz
Differential SSTL-2 *(1)*	110	100	100	MHz
LVPECL *(2)*	311	275	275	MHz
PCML *(2)*	250	200	200	MHz

Table 4–126. High-Speed I/O Specifications for Wire-Bond Packages (Part 2 of 2)

Symbol	Conditions	-6 Speed Grade			-7 Speed Grade			-8 Speed Grade			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
SW	PCML (J = 4, 7, 8, 10) only	800			800			800			ps
	PCML (J = 2) only	1,200			1,200			1,200			ps
	PCML (J = 1) only	1,700			1,700			1,700			ps
	LVDS and LVPECL (J = 1) only	550			550			550			ps
	LVDS, LVPECL, HyperTransport technology (J = 2 through 10) only	500			500			500			ps
Input jitter tolerance (peak-to-peak)	All			250			250			250	ps
Output jitter (peak-to-peak)	All			200			200			200	ps
Output t_{RISE}	LVDS	80	110	120	80	110	120	80	110	120	ps
	HyperTransport technology	120	170	200	120	170	200	120	170	200	ps
	LVPECL	100	135	150	100	135	150	100	135	150	ps
	PCML	80	110	135	80	110	135	80	110	135	ps
Output t_{FALL}	LVDS	80	110	120	80	110	120	80	110	120	ps
	HyperTransport	110	170	200	110	170	200	110	170	200	ps
	LVPECL	100	135	160	100	135	160	100	135	160	ps
	PCML	110	145	175	110	145	175	110	145	175	ps
t_{DUTY}	LVDS (J = 2 through10) only	47.5	50	52.5	47.5	50	52.5	47.5	50	52.5	%
	LVDS (J =1) and LVPECL, PCML, HyperTransport technology	45	50	55	45	50	55	45	50	55	%
t_{LOCK}	All			100			100			100	µs